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Details

Product Status	Last Time Buy
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	-
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	473-LFBGA
Supplier Device Package	473-MAPBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8308cvmagda

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Characteristic	Symbol	Recommended Value ¹	Unit
SerDes internal digital power	XCOREV _{DD}	1.0 V ± 50 mV	V
SerDes internal digital power	XCOREV _{SS}	0.0	V
SerDes I/O digital power	XPADV _{DD}	1.0 V ± 50 mV	V
SerDes analog power for PLL	SDAV _{DD}	1.0 V ± 50 mV	V
SerDes analog power for PLL	SDAV _{SS}	0	V
SerDes I/O digital power	XPADV _{SS}	0	V
Core supply voltage	V _{DD}	1.0 V ± 50 mV	V
Analog supply for e300 core APLL ²	AV _{DD1}	1.0 V ± 50 mV	V
Analog supply for system APLL ²	AV _{DD2}	1.0 V ± 50 mV	V
DDR2 DRAM I/O voltage	GV _{DD}	1.8 V ± 100 mV	V
Differential reference voltage for DDR controller	MV _{REF}	$\begin{array}{c} \text{GVDD/2} \ (0.49 \times \text{GV}_{DD} \ \text{to} \\ 0.51 \times \text{GV}_{DD}) \end{array}$	V
Standard I/O voltage (Local bus, DUART, system control and power management, eSDHC, USB, I ² C, Interrupt, Ethernet management, SPI, Miscellaneous and JTAG I/O voltage) ³	NV _{DD}	3.3 V ± 300 mV	V
eTSEC IO supply ^{4,5}	LV _{DD1} , LV _{DD2}	2.5 V ± 125 mV 3.3 V ± 300 mV	V
Analog and digital ground	V _{SS}	0.0	V
Operating temperature range ⁶	T _A /T _J	Standard = 0 to 105 Extended = -40 to 105	°C

Table 2. Recommended Operating Conditions

Notes:

¹ GV_{DD}, NV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

² This voltage is the input to the filter discussed in Section 23.2, "PLL Power Supply Filtering," and not necessarily the voltage at the AV_{DD} pin, which may be reduced from V_{DD} by the filter.

 3 NV_{DD} here refers to NV_{DDA}, NV_{DDB}, NV_{DDG}, NV_{DDH}, NV_{DDJ} and NV_{DDP_K} from the ball map.

⁴ The max value of supply voltage should be selected based on the RGMII mode. The lower range applies to RGMII mode.

 $^5\,$ LV_{DD1} here refers to NV_{DDC} and LV_{DD2} refers to NV_{DDF} from the ball map.

⁶ Minimum temperature is specified with T_A ; Maximum temperature is specified with T_J .

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



Figure 2. Overshoot/Undershoot Voltage for GVDD/NVDD/LVDD

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths.

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	NV _{DD} = 3.3 V
DDR2 signals ¹	18	GV _{DD} = 1.8 V
DUART, system control, I ² C, JTAG, eSDHC, GPIO,SPI, USB	42	NV _{DD} = 3.3 V
eTSEC signals	42	LV _{DD} = 2.5/3.3 V

Table 3. Output Drive Capability

Output Impedance can also be adjusted through configurable options in DDR Control Driver Register (DDRCDR). For more information, see the *MPC8308 PowerQUICC II Pro Processor Reference Manual*.

2.1.4 Power Sequencing

It is required to apply the core supply voltage (V_{DD}) before the I/O supply voltages (GV_{DD} , LV_{DD} , and NV_{DD}) and assert PORESET before the power supplies fully ramp up. The core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3.

If this recommendation is not observed and I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. To overcome side effects of this condition, the application environment may require tuning of external pull-up or pull-down resistors on particular signals to lesser values.

DDR2 SDRAM

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MDQ//MDM/MECC output setup with respect to MDQS	t _{DDKHDS,} t _{DDKLDS}			ps	5
266 MHz		900			
MDQ//MDM/MECC output hold with respect to MDQS	t _{DDKHDX,} t _{DDKLDX}		_	ps	5
266 MHz		1100			
MDQS preamble start	t _{DDKHMP}	0.75 x t _{MCK}		ns	6
MDQS epilogue end	t _{DDKHME}	0.4 x t _{MCK}	0.6 x t _{MCK}	ns	6

Table 18. DDR2 SDRAM Output AC Timing Specifications (continued)

Notes:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
 </sub>
- 2. All MCK/MCK referenced measurements are made from the crossing of the two signals ±0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ/MECC/MDM/MDQS.
- 4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. For a description and understanding of the timing modifications enabled by use of these bits, see the MPC8308 PowerQUICC II Pro Processor Reference Manual.
- 5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

DDR2 SDRAM

This figure shows the DDR2 SDRAM output timing for the MCK to MDQS skew measurement (tDDKHMH).



Figure 5. Timing Diagram for t_{DDKHMH}

This figure shows the DDR2 SDRAM output timing diagram.



Figure 6. DDR2 SDRAM Output Timing Diagram

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RGMII Electrical Characteristics

The electrical characteristics specified here apply to all the media independent interface (MII) and reduced gigabit media independent interface (RGMII), signals except management data input/output (MDIO) and management data clock (MDC). The RGMII interface is defined for 2.5 V, while the MII interface can be operated at 3.3 V. The RGMII interface follows the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet Physical Layer Device Specification Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 eTSEC DC Electrical Characteristics

All MII and RGMII drivers and receivers comply with the DC parametric attributes specified in Table 21 and Table 22. The RGMII signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV _{DD}		—	3.0	3.6	V
Output high voltage	V _{OH}	I _{OH} = -4.0 mA	LV _{DD} = Min	2.40	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 4.0 mA	LV _{DD} = Min	VSS	0.50	V
Input high voltage	V _{IH}	_	_	2.1	LV _{DD} + 0.3	V
Input low voltage	V _{IL}	_	_	-0.3	0.90	V
Input high current	IIH	$V_{IN}^{1} = LV_{DD}$		—	40	μΑ
Input low current	I	V _{IN}	¹ = VSS	-600	_	μΑ

Table 21. MII DC Electrical Characteristics

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Ethernet: Three-Speed Ethernet, MII Management

This figure shows the MII transmit AC timing diagram.



Figure 8. MII Transmit AC Timing Diagram

8.2.1.2 **MII Receive AC Timing Specifications**

This table provides the MII receive AC timing specifications.

Table 24. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} /NV_{DD} of 3.3 V ± 0.3V.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
RX_CLK clock period 10 Mbps	t _{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t _{MRX}	—	40	—	ns
RX_CLK duty cycle	t _{MRXH} /t _{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t _{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t _{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise V _{IL} (min) to V _{IH} (max)	t _{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time $V_{IH}(max)$ to $V_{IL}(min)$	t _{MRXF}	1.0		4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference} (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

and RGMII are specified in Section 8.1, "Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RGMII Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. This table provides the DC electrical characteristics for MDIO and MDC.

Parameter	Symbol	Cond	Min	Max	Unit	
Supply voltage (3.3 V)	NV_{DD}	-	3.0	3.6	V	
Output high voltage	V _{OH}	I _{OH} = -1.0 mA	NV _{DD} = Min	2.10	NV _{DD} + 0.3	V
Output low voltage	V _{OL}	$I_{OL} = 1.0 \text{ mA}$ $LV_{DD} = Min$		VSS	0.50	V
Input high voltage	V _{IH}	-	_	2.0	—	V
Input low voltage	V _{IL}	-	_	—	0.80	V
Input high current	I _{IH}	NV _{DD} = Max	V _{IN} ¹ = 2.1 V	—	40	μΑ
Input low current	IIL	NV _{DD} = Max	V _{IN} = 0.5 V	-600	—	μΑ

Table 26. MII Management DC Electrical Characteristics When Powered at 3.3 V

Note:

1. V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 27. MII Management AC Timing Specifications

At recommended operating conditions with $\text{LV}_{\text{DDA}}/\text{LV}_{\text{DDB}}$ is 3.3 V \pm 0.3V

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit	Notes
MDC frequency	f _{MDC}	_	2.5	—	MHz	2
MDC period	t _{MDC}	_	400	—	ns	—
MDC clock pulse width high	t _{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t _{MDKHDX}	10	—	170	ns	3
MDIO to MDC setup time	t _{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t _{MDDXKH}	0	—	—	ns	—
MDC rise time	t _{MDCR}	—	—	10	ns	—

Ethernet: Three-Speed Ethernet, MII Management

Table 27. MII Management AC Timing Specifications (continued)

At recommended operating conditions with LV_{DDA}/LV_{DDB} is 3.3 V \pm 0.3V

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit	Notes
MDC fall time	t _{MDHF}	_	_	10	ns	_

Notes:

The symbols used for timing specifications Follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

- 2. This parameter is dependent on the csb_clk speed. (The MIIMCFG[Mgmt Clock Select] field determines the clock frequency of the Mgmt Clock EC_MDC.)
- 3. This parameter is dependent on the cbs_clk speed (that is, for a csb_clk of 133 MHz, the delay is 60 ns).

This figure shows the MII management AC timing diagram.



Figure 12. MII Management Interface Timing Diagram

8.4 IEEE Std 1588[™] Timer Specifications

This section describes the DC and AC electrical specifications for the 1588 timer.

8.4.1 IEEE 1588 Timer DC Specifications

This table provides the IEEE 1588 timer DC specifications.

Table 28. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	l _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V
Input high voltage	V _{IH}	—	2.0	NVDD + 0.3	V

USB

9.1.2 USB AC Electrical Specifications

This table lists the general timing parameters of the USB-ULPI interface.

 Table 31. USB General Timing Parameters

Parameter	Symbol ¹	Min	Мах	Unit	Notes
USB clock cycle time	t _{USCK}	15	—	ns	1, 2
Input setup to USB clock—all inputs	t _{USIVKH}	4	—	ns	1, 4
Input hold to USB clock—all inputs	t _{USIXKH}	1	—	ns	1, 4
USB clock to output valid—all outputs	t _{USKHOV}	-	9	ns	1
Output hold from USB clock—all outputs	t _{USKHOX}	1		ns	1

Notes:

The symbols used for timing specifications follow the pattern of t<sub>(First two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{USIXKH} symbolizes usb timing (US) for the input (I) to go invalid (X) with respect to the time the usb clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes usb timing (US) for the usb clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub>

- 2. All timings are in reference to USB clock.
- 3. All signals are measured from NVDD/2 of the rising edge of USB clock to 0.4 × NVDD of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

The following two figures provide the AC test load and signals for the USB, respectively.



10.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the MPC8308 SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- Differential Mode
 - The input amplitude of the differential clock must be between 400 mV and 1600 mV differential peak-peak (or between 200 mV and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800 mV and greater than 200 mV. This requirement is the same for both external DC-coupled or AC-coupled connection.
 - For external DC-coupled connection, as described in Section 10.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 mV and 400 mV. Figure 17 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
 - For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to XCOREVSS. Each signal wire of the differential inputs is allowed to swing below and above the common mode voltage (XCOREVSS). Figure 18 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- Single-ended Mode
 - The reference clock can also be single-ended. The SD_REF_CLK input amplitude (single-ended swing) must be between 400 mV and 800 mV peak-peak (from Vmin to Vmax) with SD_REF_CLK either left unconnected or tied to ground.
 - The SD_REF_CLK input average voltage must be between 200 and 400 mV. Figure 19 shows the SerDes reference clock input requirement for single-ended signaling mode.
 - To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase (SD_REF_CLK) through the same source impedance as the clock input (SD_REF_CLK) in use.

High-Speed Serial Interfaces (HSSI)









Figure 19. Single-Ended Reference Clock Input DC Requirements

10.2.3 Interfacing with Other Differential Signaling Levels

With on-chip termination to XCOREVSS, the differential reference clocks inputs are high-speed current steering logic (HCSL) compatible and DC coupled.

Many other low voltage differential type outputs like low-voltage differential signaling (LVDS) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100–400 mV) for DC-coupled connection.

LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

11.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ± 300 ppm tolerance.

11.4 Physical Layer Specifications

Following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer please use the *PCI Express Base Specification*, Rev. 1.0a.

11.4.1 Differential Transmitter (TX) Output

This table defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Parameter	Symbol	Comments	Min	Typical	Max	Units	Note
Unit interval	UI	Each U_{PETX} is 400 ps ± 300 ppm. U_{PETX} does not account for Spread Spectrum Clock dictated variations.	399.88	400	400.12	ps	1
Differential peak-to-peak output voltage	V _{TX-DIFFp-p}	$V_{PEDPPTX} = 2^* V_{TX-D+} - V_{TX-D-} $	0.8	_	1.2	V	2
De-Emphasized differential output voltage (ratio)	V _{TX-DE} -RATIO	Ratio of the $V_{PEDPPTX}$ of the second and following bits after a transition divided by the $V_{PEDPPTX}$ of the first bit after a transition.	-3.0	-3.5	-4.0	dB	2
Minimum TX eye width	T _{TX-EYE}	The maximum Transmitter jitter can be derived as $T_{TX-MAX-JITTER} = 1 - U_{PEEWTX} = 0.3 UI.$	0.70	—		UI	2, 3
Maximum time between the jitter median and maximum deviation from the median	T _{TX-EYE-MEDIAN-to-} MAX-JITTER	Jitter is defined as the measurement variation of the crossing points $(V_{PEDPPTX} = 0 V)$ in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.	_	_	0.15	UI	2, 3
D+/D- TX output rise/fall time	T _{TX-RISE} , T _{TX-FALL}	_	0.125	—	_	UI	2, 5
RMS AC peak common mode output voltage	V _{TX-CM-ACp}	$V_{PEACPCMTX} = RMS(V_{TXD+} + V_{TXD-} /2 - V_{TX-CM-DC})$ $V_{TX-CM-DC} = DC_{(avg)} \text{ of } V_{TX-D+} + V_{TX-D-} /2$			20	mV	2

Table 34. Differential Transmitter (TX) Output Specifications

PCI Express



Figure 27. Minimum Transmitter Timing and Voltage Output Compliance Specifications

11.4.3 Differential Receiver (RX) Input Specifications

This table defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Parameter	Symbol	Comments	Min	Typical	Max	Units	Note
Unit interval	UI	Each U _{PERX} is 400 ps ± 300 ppm. U _{PERX} does not account for Spread Spectrum Clock dictated variations.	399.88	400	400.12	ps	1
Differential peak-to-peak output voltage	V _{RX-DIFFp-p}	$V_{PEDPPRX} = 2^* V_{RX-D+} - V_{RX-D-} $	0.175	—	1.200	V	2
Minimum receiver eye width	T _{RX-EYE}	The maximum interconnect media and Transmitter jitter that can be tolerated by the Receiver can be derived as $T_{RX-MAX-JITTER} = 1 - U_{PEEWRX} = 0.6 UI.$	0.4	—	_	UI	2, 3
Maximum time between the jitter median and maximum deviation from the median.	T _{RX-EYE-MEDIAN-to-} MAX-JITTER	Jitter is defined as the measurement variation of the crossing points ($V_{PEDPPRX} = 0 V$) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.		_	0.3	UI	2, 3, 7

Table 35. Differential Receiver (RX) Input Specifications

13.2.2 Full Speed Input Path (Read)

This figure provides the data and command input timing diagram.



Figure 36. Full Speed Input Path

13.3 eSDHC AC Timing Specifications

This table provides the eSDHC AC timing specifications.

Table 40. eSDHC AC Timing Specifications for High Speed Mode

At recommended operating conditions NV_{DD} = 3.3 V \pm 300 mV.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
SD_CLK clock frequency—high speed mode	f _{SHSCK}	0	50	MHz	3
SD_CLK clock cycle	t _{SHSCK}	20	—	ns	—
SD_CLK clock frequency—identification mode	f _{SIDCK}	0	400	kHz	—
SD_CLK clock low time	t _{SHSCKL}	7	—	ns	2
SD_CLK clock high time	t _{sнscкн}	7	—	ns	2
SD_CLK clock rise and fall times	t _{SHSCKR∕} t _{SHSCKF}	—	3	ns	2
Input setup times: SD_CMD, SD_DATx	t _{SHSIVKH}	3	—	ns	2
Input hold times: SD_CMD, SD_DATx	t _{SHSIXKH}	2	—	ns	2
Output delay time: SD_CLK to SD_CMD, SD_DATx valid	t _{SHSKHOV}	3	—	ns	2
Output Hold time: SD_CLK to SD_CMD, SD_DATx invalid	t _{SHSKHOX}	-3	_	ns	2
SD Card Input Setup	t _{ISU}	6		ns	3
SD Card Input Hold	t _{IH}	2		ns	3

14 JTAG

JTAG

This section describes the DC and AC electrical specifications for the IEEE Std 1149.1TM (JTAG) interface.

14.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the IEEE 1149.1 (JTAG) interface.

Characteristic	Symbol	Condition	Min	Max	Unit
nput high voltage	V _{IH}	_	2.1	$NV_{DD} + 0.3$	V
nput low voltage	V _{IL}	_	-0.3	0.8	V
nput current	I _{IN}	_		±5	μΑ
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	_	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

Table 41. JTAG Interface DC Electrical Characteristics

14.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface.

This table provides the JTAG AC timing specifications as defined in Figure 41 through Figure 44.

Table 42. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Мах	Unit	Note
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	—
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 4		ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	10 10		ns	4
Valid times: Boundary-scan data TDO	t _{JTKLDV} t _{JTKLOV}	2 2	11 11	ns	5

16 Timers

This section describes the DC and AC electrical specifications for the timers.

16.1 Timers DC Electrical Characteristics

This table provides the DC electrical characteristics for the MPC8308 timers pins, including TIN, TOUT, and TGATE.

Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V
Input high voltage	V _{IH}	—	2.1	$NV_{DD} + 0.3$	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0~V \leq V_{IN} \leq NV_{DD}$	—	± 5	μΑ

Table 45. Timers DC Electrical Characteristics

16.2 Timers AC Timing Specifications

This table provides the timers input and output AC timing specifications.

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Table 46. Timers Input AC Timing Specifications
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Characteristic	Symbol ¹	Min	Unit
Timers inputs—minimum pulse width	t _{TIWID}	20	ns

Notes:

1. Timers inputs and outputs are asynchronous to any visible clock. Timers outputs should be synchronized before use by any external synchronous logic. Timers inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation

This figure provides the AC test load for the Timers.



Figure 47. Timers AC Test Load

Package and Pin Listings

This figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.



This figure shows the SPI timing in master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 51. SPI AC Timing in Master Mode (Internal Clock) Diagram

20 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8308 is available in a moulded array process ball grid array (MAPBGA). For information on the MAPBGA, see Section 20.1, "Package Parameters for the MPC8308 MAPBGA," and Section 20.2, "Mechanical Dimensions of the MPC8308 MAPBGA."

20.1 Package Parameters for the MPC8308 MAPBGA

The package parameters are as provided in the following list. The package type is $19 \text{ mm} \times 19 \text{ mm}$, 473 MAPBGA.

Package outline	19 mm × 19 mm
Interconnects	473
Pitch	0.80 mm
Module height (typical)	1.39 mm
Solder Balls	96.5 Sn/ 3.5Ag
Ball diameter (typical)	0.40 mm

22.1 Thermal Characteristics

This table provides the package thermal characteristics for the 473, 19×19 mm MAPBGA.

Characteristic	Board Type	Symbol	Value	Unit	Note
Junction to Ambient Natural Convection	Single layer board (1s)	$R_{ ext{ heta}JA}$	42	°C/W	1, 2
Junction to Ambient Natural Convection	Four layer board (2s2p)	$R_{ hetaJA}$	27	°C/W	1, 2, 3
Junction to Ambient (@200 ft/min)	Single layer board (1s)	R_{\thetaJMA}	35	°C/W	1, 3
Junction to Ambient (@200 ft/min)	Four layer board (2s2p)	R_{\thetaJMA}	24	°C/W	1, 3
Junction to Board	—	$R_{ heta JB}$	17	°C/W	4
Junction to Case	—	$R_{ ext{ heta}JC}$	9	°C/W	5
Junction to Package Top	Natural Convection	Ψ_{JT}	2	°C/W	6

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

- 2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
- 3. Per JEDEC JESD51-6 with the board horizontal.
- 4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

22.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

22.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

 T_I = junction temperature (°C)

 T_A = ambient temperature for the package (°C)

 $R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

The junction-t-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single layer board is

24.2 Part Marking

Parts are marked as in the example shown in this figure.



CCCCC is the country code. MMMMM is the mask number. YWWLAZ is the assembly traceability code.

Figure 56. Freescale Part Marking for PBGA Devices

This table lists the SVR settings.

Table 62. SVR Settings

Device	Package	SVR
MPC8308	MAPBGA	0x8101 _0110

Note: PVR = 8085_0020 for the device.

25 Document Revision History

This table summarizes a revision history for this document.

Table 63.	Document	Revision	History
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Rev. Number	Date	Substantive Change(s)
3	10/2011	 In Section 2.1.4, "Power Sequencing," changed description. In Table 53, updated GPIOs pins as I/O. In Table 54, removed PCI Express = csb_clk/2 and csb_clk/3 options. In Table 61, added note 4.
2	02/2011	 Added NV_{DDJ} to Note-7 in Table 1. In Table 2, Added Note-2 Added NV_{DDJ} to Note-3 Added "Extended Temperature range from -40 to 105 °C, in the last row of the table Changed "characteristic name Junction temperature" to "Operating temperature range" In Table 4, Note-3, changed ambient temperature to junction temperature, T_J = 105° C In Table 18, t_{DDKHCS} changed from 3.15ns to 2.5ns t_{DDKHMP} and t_{DDKHME} values updated In Figure 6, corrected t_{DDKHMP} & t_{DDKHME} waveform In Table 53, Y23 Package Pin Number changed from NC to V_{DD} signal group TSEC2_CRS is muxed with GPIO[0], shown as TSEC2_CRS/ GPIO[0] In Table 58, note-1, core_clk maximum operating frequency 333 MHz replaced with 400 MHz
1	06/2010	• In Table 4, $T_A = 105$ replaced with $T_J = 105$ • In Table 8, $f_{SYS_CLK_IN}$ (Max) = 66 replaced with 66.67 and $t_{SYS_CLK_IN}$ (Min) = 15.15 replaced with 15 • In Table 53, TSEC1_TMR_RX_ESFD replaced with TSEC2_TMR_RX_ESFD TSEC1_TMR_TX_ESFD replaced with TSEC2_TMR_TX_ESFD TSEC0_TMR_RX_ESFD replaced with TSEC1_TMR_RX_ESFD TSEC0_TMR_TX_ESFD replaced with TSEC1_TMR_TX_ESFD • In Table 56, rows from 1000 to 1111 removed • In Table 57, SPMF 5:1 Option 167 MHz added.
0	05/2010	Initial release